

Integrated AC LED Solution

Acrich3 - 30.0W SMJD-XD30W4PF









Product Brief

Description

- The Acrich3 COB series of products are designed to be small LES. and driven directly off of AC line voltage, therefore they do not need the standard converter essential for conventional general lighting products.
- The converter or driver found in most general lighting products can limit the overall life of the product, but with the Acrich3 series of products the life of the product can more closely be estimated from the LED itself. This will also allow for a much smaller form factor from an overall fixture design allowing for higher creativity in the fixture.
- The modules have a high power factor which can contribute to a higher energy savings in the end application.

Features and Benefits

- Small LES
- · Connects directly to AC line voltage
- Low THD
- Long Life Time
- Simple BOM
- Miniaturization
- Lead Free Product
- RoHS Compliant
- TRIAC Dimming

Key Applications

Down Llight

Table 1. Product Selection (CCT)

Part No.	Vin [Vac]	P [W]	Color	сст [к]	CRI Min.
			Cool	4700 – 7000	
SMJD-2D30W4PF SMJD-3D30W4PF	120 220	30.0 Neutral	3700 – 4700	80	
			Warm	2600 – 3700	

Table 2. Product Selection (Flux)

Part No.	Vin [Vac]	P [W]	Flux	Flux [lm]		
Fait No.	VIII [Vac]	L [vv]	Min.	Тур.	Remark	
SMJD-2D30W4PF	120	120 30.0	2820	3230	30b	
SMJD-3D30W4PF	220	30.0	3230	3730	30c	

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Performance Characteristics

Table 3. Electro Optical Characteristics, T_a = 25°C

	0		Value		1124	Marila
Parameter	Symbol	Min.	Тур.	Max.	Unit	Mark
Luminous Flux	Φ _V ^[2]	2820	3230	-	· Im	30b
Luminous Flux	Ψ _V ι-ι	3230	3730		· IIII	30c
		6000	6500	7000		А
		5300	5700	6000		В
		4700	5000	5300	•	С
Correlated Color	007	4200	4500	4700		D
Temperature [3]	ССТ	3700	4000	4200	· K	E
		3200	3500	3700		F
		2900	3000	3200	•	G
		2600	2700	2900	•	Н
CRI	Ra	80	-	-	-	F
Lanut Valtana [4]	M		120		\/	2D
Input Voltage [4]	V_{in}		220		· Vac	3D
Power Consumption	Power Consumption P		30.0	33.0	W	30W
Operating Frequency	Operating Frequency F		50 / 60		Hz	
Power Factor	Power Factor PF		Over 0.9		-	
Viewing Angle	20 _{1/2}		120		deg.	
Tolerance of Surge [5]	V _s	500	-	-	V	

Notes:

- (1) At 120 or 220Vac, $T_a = 25^{\circ}C$
- (2) Φ_{V} is the total luminous flux output measured with an integrated sphere.
- (3) Integrated sphere measure tolerance : \pm 5%
- (4) Correlated Color Temperature is derived from the CIE 1931 Chromaticity diagram.
- (5) Operating Voltage doesn't indicate the maximum voltage which customers use but means tolerable voltage according to each country's voltage variation rate. It is recommended that the solder pad temperature should be below 70 °C.
- (6) Surge withstand in accordance with IEC61000-4-5



Performance Characteristics

Table 4. Absolute Maximum Ratings, T_a = 25°C

Parameter	Symbol	Unit	Value
Maximum Input Voltage	V_{in}	Vac	144 (@120V) 264 (@220V)
Power Consumption	Р	W	33.0
Operating Temperature	T _c	°C	<70
Storage Temperature	T_{stg}	°C	-40 ~ 100
ESD Sensitivity	-	-	±4,000V HBM

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Thermal Resistance

Part	Package Power Dissipation [W]	Maximum Junction Temperature [℃]	Rθ _{j-s} [℃/W]
Acrich3 LED	SAW87F1D Max 33	140	0.83

Notes:

The MJT COB has a thermal resistance of 0.83 $^{\circ}\text{C/W}$ from junction of the COB to the

COB slug.

The maximum junction temperature of the MJT COB package is $140\,^{\circ}$ C, therefore the maximum lead temperature T_{s max} is

$$T_{s_max} = T_{j_max} - (R\theta_{j-s} * P_d)$$

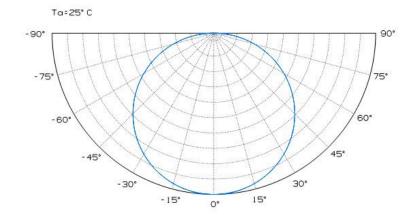
= 140°C - (0.83°C/W * 33W) = 112.6°C

Although this is the maximum lead temperature, it is recommended to keep the COB slug under $70\,^{\circ}$ C.

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Characteristics Graph

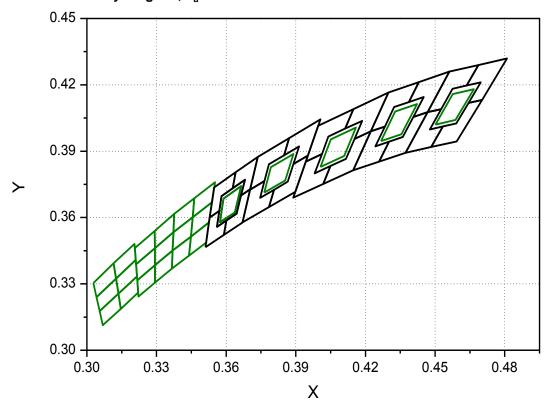
Fig 1. Radiant Pattern, T_a =25 ℃



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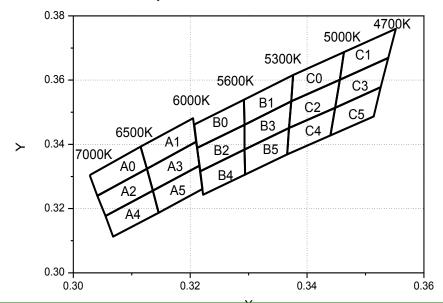
Color Bin Structure

CIE Chromaticity Diagram, $T_a = 25 \,^{\circ}$ C



- 1. Energy Star binning applied to all 2600~7000K.
- 2. Measurement uncertainty of the Color Coordinates: ± 0.005

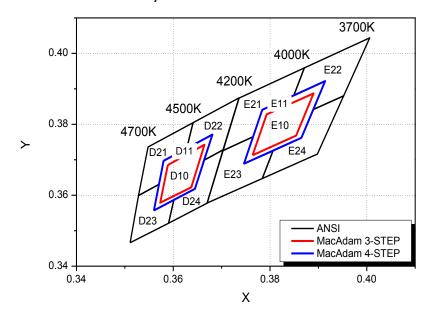
Color Bin Structure



	\ 0	А	1	А	2
CIE x	CIE y	CIE x	CIE y	CIE x	CIE y
0.3028	0.3304	0.3115	0.3393	0.3041	0.324
0.3041	0.324	0.3126	0.3324	0.3055	0.3177
0.3126	0.3324	0.321	0.3408	0.3136	0.3256
0.3115	0.3393	0.3205	0.3481	0.3126	0.3324
	13	A	4	А	
CIE x	CIE y	CIE x	CIE y	CIE x	CIE y
0.3126	0.3324	0.3055	0.3177	0.3136	0.3256
0.3136	0.3256	0.3068	0.3113	0.3146	0.3187
0.3216	0.3334	0.3146	0.3187	0.3221	0.3261
0.321	0.3408	0.3136	0.3256	0.3216	0.3334
	0	С	1	С	2
CIE x	CIE y	CIE x	CIE y	CIE x	CIE y
0.3376	0.3616	0.3463	0.3687	0.3373	0.3534
0.3373	0.3534	0.3456	0.3601	0.3369	0.3451
0.3456	0.3601	0.3539	0.3669	0.3448	0.3514
0.3463	0.3687	0.3552	0.3760	0.3456	0.3601
	3	С	4	С	5
CIE x	CIE y	CIE x	CIE y	CIE x	CIE y
0.3456	0.3601	0.3369	0.3451	0.3448	0.3514
0.3448	0.3514	0.3366	0.3369	0.3440	0.3428
0.3526	0.3578	0.3440	0.3428	0.3514	0.3487
0.3539	0.3669	0.3448	0.3514	0.3526	0.3578
	0	C		С	2
CIE x	CIE y	CIE x	CIE y	CIE x	CIE y
0.3376	0.3616	0.3463	0.3687	0.3373	0.3534
0.3373	0.3534	0.3456	0.3601	0.3369	0.3451
0.3456	0.3601	0.3539	0.3669	0.3448	0.3514
0.3463	0.3687	0.3552	0.3760	0.3456	0.3601
	3	C		C	5
CIE x	CIE y	CIE x	CIE y	CIE x	CIE y
0.3456	0.3601	0.3369	0.3451	0.3448	0.3514
0.3448	0.3514	0.3366	0.3369	0.3440	0.3428
0.3526	0.3578	0.3440	0.3428	0.3514	0.3487
0.3539	0.3669	0.3448 0.3514 0.352		0.3526	0.3578

Color Bin Structure

CIE Chromaticity Diagram, T_j=85 ℃, I_F=20mA

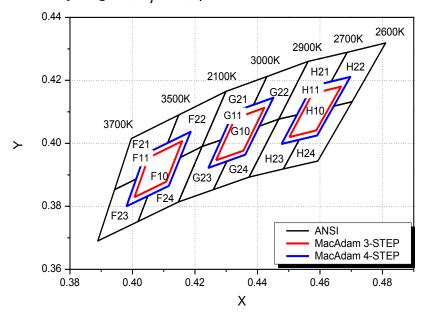


	3-S ⁻	ТЕР			4-S1	ΓEP	
D 1	10	E1	10	D.	11	E.	11
CIE x	CIE y	CIE x	CIE y	CIE x	CIE y	CIE x	CIE y
0.3589	0.3685	0.3764	0.3713	0.3560	0.3557	0.3746	0.3689
0.3665	0.3742	0.3793	0.3828	0.3580	0.3697	0.3784	0.3841
0.3637	0.3622	0.3890	0.3887	0.3681	0.3771	0.3914	0.3922
0.3573	0.3579	0.3854	0.3768	0.3645	0.3618	0.3865	0.3762

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Color Bin Structure

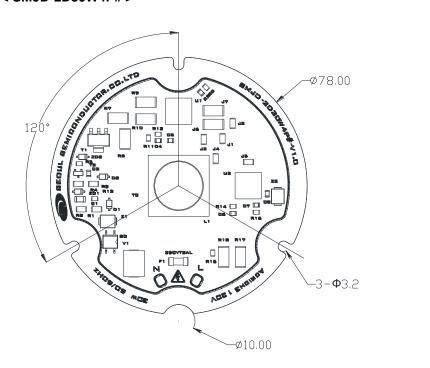
CIE Chromaticity Diagram, T_j=85 °C, I_F=20mA



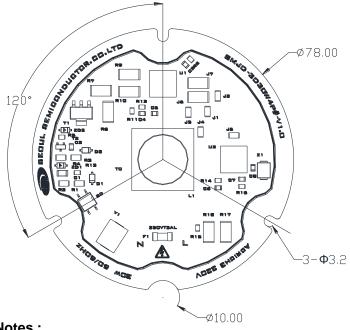
	3-STEP							4-S	TEP		
F1	10	G.	10	H [.]	10	F ²	11	G	11	H	11
CIE x	CIE y	CIE x	CIE y	CIE x	CIE y	CIE x	CIE y	CIE x	CIE y	CIE x	CIE y
0.4006	0.3829	0.4267	0.3946	0.4502	0.4020	0.3981	0.3800	0.4243	0.3922	0.4477	0.3998
0.4051	0.3954	0.4328	0.4079	0.4576	0.4158	0.4040	0.3966	0.4324	0.4100	0.4575	0.4182
0.4159	0.4007	0.4422	0.4113	0.4667	0.4180	0.4186	0.4037	0.4451	0.4145	0.4697	0.4211
0.4108	0.3878	0.4355	0.3977	0.4588	0.4041	0.4116	0.3865	0.4361	0.3964	0.4591	0.4025

Mechanical Dimensions

< SMJD-2D30W4P# >



< SMJD-3D30W4P# >



1.60--4.80

4.80-

(1) All dimensions are in millimeters. (Tolerance : ± 0.2)

(2) Scale: None



Marking Information



A: ex) 150101 FbJG11

2

- Description

150101 (1) F bJ G 1 1 (6) (5) (4) (3)

- ① SMT Date (YYMMDD, 6 Digits)
- 2 CRI (1 Digits)
- 3 Module Flux Bin (2 Digits)
- 4 CCT (1 Digit)
- 5 CCT Combination NO. (1 Digit)
- 6 VF Combination NO. (1 Digit)

A: Marking

	② CRI		③ Module Flux Bin			CC			⑥ VF Bin	
Mark	CRI	Туре	Mark	Min.	Тур.	Mark	Bin	Mark	Min.	Max.
F	80	b	bJ	2820	3230	*0	*0	1	F	F
		С	cK	3230	3730	*1	*1	2	G	G
						*2	*2			
						*3	*3			
						*4	*4			
						*5	*5			
						*A	*10			
						*B	*11	•		

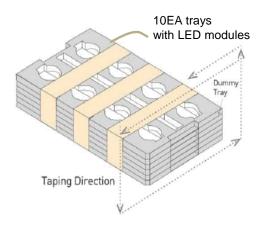
^{*} CCT Mark from *0 to *4 is 3-step

Packing Information

1. Tray information

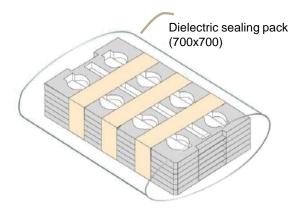


- 24 PCS LED modules packed per tray
- 2. Tray stack and taping

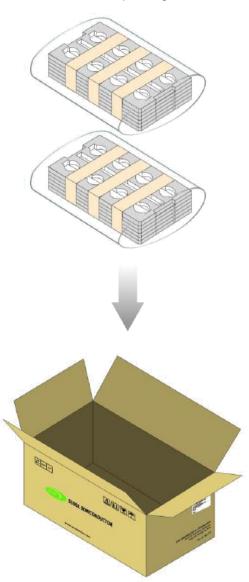


- 10 LED module trays and additional 1 dummy trays each up and down of box
- Add silica gel (1EA) on top of the tray

3. Sealing packing



4. Box information & packing



- 240 PCS modules per BOX 1EA
- 1 Box : 24 PCS per tray x 10 trays = 240 PCS

Label Information

Model No.	SMJD-2D30W4PF (1)
Rank	30bG80A ⁽²⁾
Туре	AII ⁽³⁾
Quantity	XX
Date	YYMDDXXXXX-XXXXXXX
SEOUL	SEOUL SEMICONDUCTOR CO.,LTD.

Notes

(1) The model number designation is explained as follow

SMJD : Seoul Semiconductor internal code 2D : Input voltage (120V = 2D, 220V = 3D)

30W : About Power Consumption

4: Acrich IC Version 3.0

PF: MJT COB (PF=SAW87F1D)

(2) It represents module optical SPEC'

08b : Luminous flux (08b, 08c)

G: CCT (H,G,E,C,B,A)

80 : CRI (CRI80 = 80, CRI90=90)

A: CIE Area (3step = 3, 4step = 4, A = AII)

(3) It represents module CIE SPEC'.

ALL: CIE Area (3step, 4step, All)

(4) It is attached to the top of a sealing pack & the bottom right corner of the box.

TOTAL Quantity III III III III XX



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Notes

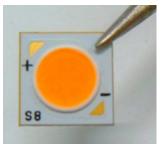


Handling of Silicone Resin for LEDs

(1) During processing, mechanical stress on the surface should be minimized as much as possible. Sharp objects of all types should not be used to pierce the sealing compound.



(2) In general, LEDs should only be handled from the side. By the way, this also applies to LEDs without a silicone sealant, since the surface can also become scratched.



- (3) Silicone differs from materials conventionally used for the manufacturing of LEDs. These conditions must be considered during the handling of such devices. Compared to standard encapsulants, silicone is generally softer, and the surface is more likely to attract dust. As mentioned previously, the increased sensitivity to dust requires special care during processing. In cases where a minimal level of dirt and dust particles cannot be guaranteed, a suitable cleaning solution must be applied to the surface after the soldering of wire.
- (4) Seoul Semiconductor suggests using isopropyl alcohol for cleaning. In case other solvents are used, it must be assured that these solvents do not dissolve the package or resin.
 Ultrasonic cleaning is not recommended. Ultrasonic cleaning may cause damage to the LED.
- (5) Please do not mold this product into another resin (epoxy, urethane, etc) and do not handle this product with acid or sulfur material in sealed space.
- (6) Avoid leaving fingerprints on silicone resin parts.

Precaution for Use

(1) Storage

To avoid the moisture penetration, we recommend storing Power LEDs in a dry box with a desiccant

The recommended storage temperature range is 5C to 30C and a maximum humidity of 50%.

- (2) Use Precaution after Opening the Packaging. Pay attention to the following:
 - a. Recommend conditions after opening the package
 - Sealing
 - Temperature : 5 ~ 40 °C Humidity : less than RH30%
 - b. If the package has been opened more than 4 week or the color of the desiccant changes.
- (3) For manual soldering

Seoul Semiconductor recommends the soldering condition

(ZC series product is not adaptable to reflow process)

- a. Use lead-free soldering
- b. Soldering should be implemented using a soldering equipment at temperature lower than 350°C.
- c. Before proceeding the next step, product temperature must be stabilized at room temperature.
- (4) Components should not be mounted on warped (non coplanar) portion of PCB.
- (5) Radioactive exposure is not considered for the products listed here in.
- (6) It is dangerous to drink the liquid or inhale the gas generated by such products when chemically disposed of.
- (7) This device should not be used in any type of fluid such as water, oil, organic solvent and etc. When washing is required, IPA (Isopropyl Alcohol) should be used.
- (8) When the LEDs are in operation the maximum current should be decided after measuring the package temperature.
- (9) LEDs must be stored properly to maintain the device. If the LEDs are stored for 3 months or more after being shipped from Seoul Semiconductor, a sealed container with vacuum atmosphere should be used for storage.
- (10) The appearance and specifications of the product may be modified for improvement without notice.

Precaution for Use

- (11) Long time exposure of sun light or occasional UV exposure will cause silicone discoloration.
- (12) Attaching LEDs, do not use adhesive that outgas organic vapor.
- (13) The driving circuit must be designed to allow forward voltage only when it is ON or OFF. If the reverse voltage is applied to LED, migration can be generated resulting in LED damage.
- (14) Please do not touch any of the circuit board, components or terminals with bare hands or metal while circuit is electrically active.
- (15) VOCs (Volatile organic compounds) emitted from materials used in the construction of fixtures can penetrate silicone encapsulants of LEDs and discolor when exposed to heat and photonic energy. The result can be a significant loss of light output from the fixture. Knowledge of the properties of the materials selected to be used in the construction of fixtures can help prevent these issues.
- (16) LEDs are sensitive to Electro-Static Discharge (ESD) and Electrical Over Stress (EOS). Below is a list of suggestions that Seoul Semiconductor purposes to minimize these effects.
- a. ESD (Electro Static Discharge)

Electrostatic discharge (ESD) is the defined as the release of static electricity when two objects come into contact. While most ESD events are considered harmless, it can be an expensive problem in many industrial environments during production and storage. The damage from ESD to an LEDs may cause the product to demonstrate unusual characteristics such as:

- Increase in reverse leakage current lowered turn-on voltage
- Abnormal emissions from the LED at low current

The following recommendations are suggested to help minimize the potential for an ESD event. One or more recommended work area suggestions:

- Ionizing fan setup
- ESD table/shelf mat made of conductive materials
- ESD safe storage containers

One or more personnel suggestion options:

- Antistatic wrist-strap
- Antistatic material shoes
- Antistatic clothes

Environmental controls:

- Humidity control (ESD gets worse in a dry environment)



Precaution for Use

b. EOS (Electrical Over Stress)

Electrical Over-Stress (EOS) is defined as damage that may occur when an electronic device is subjected to a current or voltage that is beyond the maximum specification limits of the device. The effects from an EOS event can be noticed through product performance like:

- Changes to the performance of the LED package
 (If the damage is around the bond pad area and since the package is completely encapsulated the package may turn on but flicker show severe performance degradation.)
- Changes to the light output of the luminaire from component failure
- Components on the board not operating at determined drive power

Failure of performance from entire fixture due to changes in circuit voltage and current across total circuit causing trickle down failures. It is impossible to predict the failure mode of every LED exposed to electrical overstress as the failure modes have been investigated to vary, but there are some common signs that will indicate an EOS event has occurred:

- Damaged may be noticed to the bond wires (appearing similar to a blown fuse)
- Damage to the bond pads located on the emission surface of the LED package (shadowing can be noticed around the bond pads while viewing through a microscope)
- Anomalies noticed in the encapsulation and phosphor around the bond wires.
- This damage usually appears due to the thermal stress produced during the EOS event.
- c. To help minimize the damage from an EOS event Seoul Semiconductor recommends utilizing:
 - A surge protection circuit
 - An appropriately rated over voltage protection device
 - A current limiting device



Company Information

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Company Information

Seoul Semiconductor (SeoulSemicon.com) manufacturers and packages a wide selection of light emitting diodes (LEDs) for the automotive, general illumination/lighting, appliance, signage and back lighting markets. The company is the world's fifth largest LED supplier, holding more than 10,000 patents globally, while offering a wide range of LED technology and production capacity in areas such as "nPola", deep UV LEDs, "Acrich", the world's first commercially produced AC LED, and "Acrich MJT - Multi-Junction Technology" a proprietary family of high-voltage LEDs. The company's broad product portfolio includes a wide array of package and device choices such as Acrich, high-brightness LEDs, mid-power LEDs, side-view LEDs, through-hole type LED lamps, custom displays, and sensors. The company is vertically integrated from epitaxial growth and chip manufacture in it's fully owned subsidiary, Seoul Viosys, through packaged LEDs and LED modules in three Seoul Semiconductor manufacturing facilities. Seoul Viosys also manufactures a wide range of unique deep-UV wavelength devices.

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Revision History

Revision	Date	Page	Remarks
0.0	2015-10-30	All	Initial release